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TABLE OF CONTENTS

1.1 The Age of Sensors – How MEMS Sensors Will Enable the Next Wave of New Products	1
<i>S. Lloyd, M. Lim</i>	
1.2 Intelligent Mobility Realized through VLSI	5
<i>T. Asami</i>	
2.1 Si FinFET Based 10nm Technology with Multi Vt Gate Stack for Low Power and High Performance Applications	9
<i>H.-J. Cho, H. S. Oh, K. J. Nam, Y. H. Kim, K. H. Yeo, W. D. Kim, Y. S. Chung, Y. S. Nam, S. M. Kim, W. H. Kwon, M. J. Kang, I. R. Kim, H. Fukutome, C. W. Jeong, H. J. Shin, Y. S. Kim, D. W. Kim, S. H. Park, H. S. Oh, J. H. Jeong, S. B. Kim, D. W. Ha, J. H. Park, H. S. Rhee, S. J. Hyun, D. S. Shin, D. H. Kim, H. Y. Kim, S. Maeda, K. H. Lee, Y. H. Kim, M. C. Kim, Y. S. Koh, B. Yoon, K. Shin, N. I. Lee, S. B. Kangh, K. H. Hwang, J. H. Lee, J.-H. Ku, S. W. Nam, S. M. Jung, H. K. Kang, J. S. Yoon, E. S. Jung</i>	
2.2 FINFET Technology Featuring High Mobility SiGe Channel for 10nm and Beyond	11
<i>D. Guo, G. Karve, G. Tsutsui, K.-Y. Lim, R. Robison, T. Hook, R. Vega, D. Liu, S. Bedell, S. Mochizuki, F. Lie, K. Akarvardar, M. Wang, R. Bao, S. Burns, V. Chan, K. Cheng, J. Demarest, J. Fronheiser, P. Hashemi, J. Kelly, J. Li, N. Loubet, P. Montanini, B. Sahu, M. Sankarapandian, S. Sieg, J. Sporre, J. Strane, R. Southwick, N. Tripathi, R. Venigalla, J. Wang, K. Watanabe, C. W. Yeung, D. Gupta, B. Doris, N. Felix, A. Jacob, H. Jagannathan, S. Kanakasabapathy, R. Mo, V. Narayanan, D. Sadana, P. Oldiges, J. Stathis, T. Yamashita, V. Paruchuri, M. Colburn, A. Knorr, R. Divakaruni, H. Bu, M. Khare</i>	
2.3 High Performance In_{0.53}Ga_{0.47}As FinFETs Fabricated on 300 mm Si Substrate	13
<i>M. L. Huang, S. W. Chang, M. K. Chen, Y. Oniki, H. C. Chen, C. H. Lin, W. C. Lee, C. H. Lin, M. A. Khaderbad, K. Y. Lee, Z. C. Chen, P. Y. Tsai, L. T. Lin, M. H. Tsai, C. L. Hung, T. C. Huang, Y. C. Lin, Y.-C. Yeo, S. M. Jang, H. Y. Hwang, H. C.-H. Wang, C. H. Diaz</i>	
2.4 Achieving Sub-ns switching of STT-MRAM for Future Embedded LLC Applications through Improvement of Nucleation and Propagation Switching Mechanisms	15
<i>G. Jan, L. Thomas, S. Le, Y.-J. Lee, H. Liu, J. Zhu, J. Iwata-Harms, S. Patel, R.-Y. Tong, S. Serrano-Guisan, D. Shen, R. He, J. Haq, J. Teng, V. Lam, R. Annapragada, Y.-J. Wang, T. Zhong, T. Tornng, P.-K. Wang</i>	
3.1 Memory in the Era of Innovative Architectures	17
<i>D. Klein</i>	
3.2 High-Density User-Programmable Logic Array Based on Adjacent Integration of Pure-CMOS Crossbar Antifuse into Logic CMOS Circuits	19
<i>S. Yasuda, M. Oda, M. Matsumoto, K. Tatumura, K. Zaitzu, Y.-H. Ho, M. Ono</i>	
3.3 Advanced Non-Volatile Embedded Memory for a Wide Range of Applications	21
<i>S. Kimura</i>	
3.4 Random Soft Error Suppression by Stoichiometric Engineering: CMOS Compatible and Reliable 1Mb HfO₂-ReRAM with 2 Extra Masks for Embedded IoT Systems	23
<i>C. Ho, T. Y. Shen, P. Y. Hsu, S. C. Chang, S. Y. Wen, M. H. Lin, P. K. Wang, S. C. Liao, C. S. Chou, K. M. Peng, C. M. Wu, W. H. Chang, Y. H. Chen, F. Chen, L. W. Lin, T. H. Tsai, S. F. Lim, C. J. Yang, M. H. Shieh, H. H. Liao, C. H. Lin, P. L. Pai, T. Y. Chan, Y. C. Chiao</i>	
4.1 Understanding Charge Traps for Optimizing Si-Passivated Ge nMOSFETs	25
<i>P. Ren, R. Gao, Z. Ji, H. Arimura, J. F. Zhang, R. Wang, M. Duan, W. Zhang, J. Franco, S. Sioncke, D. Cott, J. Mitard, L. Witters, H. Mertens, B. Kaczer, A. Mocuta, N. Collaert, D. Linten, R. Huang, A. V.-Y. Thean, G. Groeseneken</i>	
4.2 A 2nd Generation of 14/16nm-Node Compatible Strained-Ge pFINFET with Improved Performance with Respect to Advanced Si-Channel FinFETs	27
<i>J. Mitard, L. Witters, Y. Sasaki, H. Arimura, A. Schulze, R. Loo, L.-å. Ragnarsson, A. Hikavy, D. Cott, T. Chiarella, S. Kubicek, H. Mertens, R. Ritzenthaler, C. Vrancken, P. Favia, H. Bender, N. Horiguchi, K. Barla, D. Mocuta, A. Mocuta, N. Collaert, A. V.-Y. Thean</i>	
4.3 Selective GeO_x-Scavenging from Interfacial Layer on Si_{1-x}Ge_x Channel for High Mobility Si/Si_{1-x}Ge_x CMOS Application	29
<i>C. H. Lee, H. Kim, P. Jamison, R. G. Southwick III, S. Mochizuki, K. Watanabe, R. Bao, R. Galatage, S. Guillaumet, T. Ando, R. Pandey, A. Konar, B. Lherreron, J. Fronheiser, S. Siddiqui, H. Jagannathan, V. Paruchuri</i>	
4.4 Demonstration of Record SiGe Transconductance and Short-Channel Current Drive in High-Ge-Content SiGe PMOS FinFETs with Improved Junction and Scaled EOT	31
<i>P. Hashemi, K.-L. Lee, T. Ando, K. Balakrishnan, J. A. Ott, S. Koswatta, S. U. Engelmann, D.-G. Park, V. Narayanan, R. T. Mo, E. Leobandung</i>	

5.1 Demonstration of an InGaAs Gate Stack with Sufficient PBTI Reliability by Thermal Budget Optimization, Nitridation, High-k Material Choice, and Interface Dipole	33
<i>J. Franco, A. Vais, S. Sioncke, V. Putcha, B. Kaczer, B.-S. Shie, X. Shi, R. Mahlouji, L. Nyns, D. Zhou, N. Waldron, J. W. Maes, Q. Xie, M. Givens, F. Tang, X. Jiang, H. Arimura, T. Schram, L.-å. Ragnarsson, A. S. Hernandez, G. Hellings, N. Horiguchi, M. Heyns, G. Groeseneken, D. Linten, N. Collaert, A. Thean</i>	
5.2 Application of CVS and VRS Method for Correlation of Logic CMOS Wear Out to Discrete Device Degradation Based on Ring Oscillator Circuits	35
<i>A. Kerber, T. Nigam</i>	
5.3 Deep Insight into Process-Induced Pre-Existing Traps and PBTI Stress-Induced Trap Generations in High-k Gate Dielectrics through Systematic RTN Characterizations and <i>Ab initio</i> Calculations	37
<i>J. Chen, Y. Nakasaki, Y. Mitani</i>	
5.4 Hot Carrier Degradation in Nanowire Transistors: Physical Mechanisms, Width Dependence and Impact of Self-Heating	39
<i>A. Laurent, X. Garros, S. Barraud, G. Mariniello, G. Reimbold, D. Roy, E. Vincent, G. Ghibaudo</i>	
6.1 MoS₂ U-Shape MOSFET with 10 nm Channel Length and Poly-Si Source/Drain Serving as Seed for Full Wafer CVD MoS₂ Availability	41
<i>K.-S. Li, B.-W. Wu, L.-J. Li, M.-Y. Li, C.-C. K. Cheng, C.-L. Hsu, C.-H. Lin, Y.-J. Chen, C.-C. Chen, C.-T. Wu, M.-C. Chen, J.-M. Shieh, W.-K. Yeh, Y.-L. Chueh, F.-L. Yang, C. Hu</i>	
6.2 Serially Connected Monolayer MoS₂ FETs with Channel Patterned by a 7.5 nm Resolution Directed Self-Assembly Lithography	43
<i>A. Nourbakhsh, A. Zubair, A. Tavakkoli, R. Sajjad, X. Ling, M. Dresselhaus, J. Kong, K. K. Berggren, D. Antoniadis, T. Palacios</i>	
6.3 GDOT: A Graphene-Based Nanofunction for Dot-Product Computation	45
<i>N. C. Wang, S. K. Gonugondla, I. Nahlus, N. R. Shanbhag, E. Pop</i>	
6.4 Extremely Low Power C-Axis Aligned Crystalline In-Ga-Zn-O 60 nm Transistor Integrated with Industry 65 nm Si MOSFET for IoT Normally-Off CPU Application	47
<i>S. H. Wu, X. Y. Jia, M. Kui, C. C. Shuai, T. Y. Hsieh, H. C. Lin, D. Chen, C. B. Lin, J. Y. Wu, T. R. Yew, Y. Endo, K. Kato, S. Yamazaki</i>	
6.5 A Sub-ns Three-Terminal Spin-Orbit Torque Induced Switching Device	49
<i>S. Fukami, T. Anekawa, A. Ohkawara, C. Zhang, H. Ohno</i>	
6.6 Si CMOS Platform for Quantum Information Processing	51
<i>L. Hutin, R. Maurand, D. Kotekar-Patil, A. Corna, H. Bohuslavskyi, X. Jehl, S. Barraud, S. De Franceschi, M. Sanquer, M. Vinet</i>	
7.1 Ultralow-Resistivity CMOS Contact Scheme with Pre-Contact Amorphization Plus Ti (Germano-)Silicidation	53
<i>H. Yu, M. Schaeckers, A. Hikavy, E. Rosseel, A. Peter, K. Hollar, F. A. Khaja, W. Aderhold, L. Date, A. J. Mayur, J.-G. Lee, K. M. Shin, B. Douhard, S. A. Chew, S. Demuyne, S. Kubicek, D. Kim, A. Mocuta, K. Barla, N. Horiguchi, N. Collaert, A. V.-Y. Thean, K. De Meyer</i>	
7.2 Ti and NiPt/Ti Liner Silicide Contacts for Advanced Technologies	55
<i>P. Adusumilli, E. Alptekin, M. Raymond, N. Breil, F. Chafik, C. Lavoie, D. Ferrer, S. Jain, V. Kamini, A. Ozcan, S. Allen, J. J. An, V. Basker, R. Bolam, H. Bu, J. Cai, J. Demarest, B. Doris, E. Engbrecht, S. Fan, J. Fronheiser, O. Gluschenkov, D. Guo, B. Haran, D. Hilscher, H. Jagannathan, D. Kang, Y. Ke, J. Kim, S. Koswatta, A. Kumar, A. Labonte, R. Lallement, W. Lee, Y. Lee, J. Li, C.-H. Lin, B. Liu, Z. Liu, N. Loubet, N. Makela, S. Mochizuki, B. Morgenfeld, S. Narasimha, T. Nesheiwat, H. Niimi, C. Niu, M. Oh, C. Park, R. Ramachandran, J. Rice, V. Sardesai, J. Shearer, C. Sheraw, C. Tran, G. Tsutsui, H. Utomo, K. Wong, R. Xie, T. Yamashita, Y. Yan, C. Yeh, M. Yu, N. Zamdmer, N. Zhan, B. Zhang, V. Paruchuri, C. Goldberg, W. Kleemeier, S. Stiffler, R. Divakaruni, W. Henson</i>	
7.3 Ultra-Low NMOS Contact Resistivity Using a Novel Plasma-Based DSS Implant and Laser Anneal for Post 7 nm Nodes	57
<i>C.-N. Ni, K. V. Rao, F. Khaja, S. Sharma, S. Tang, J. J. Chen, K. E. Hollar, N. Breil, X. Li, M. Jin, C. Lazik, J. Lee, H. Maynard, N. Variam, A. J. Mayur, S. Kim, H. Chung, M. Chudzick, R. Hung, N. Yoshida, N. Kim</i>	
7.5 Ultra Low p-Type SiGe Contact Resistance FinFETs with Ti Silicide Liner Using Cryogenic Contact Implantation Amorphization and Solid-Phase Epitaxial Regrowth (SPER)	59
<i>Y. R. Yang, N. Breil, C. Y. Yang, J. Hsieh, F. Chiang, B. Colombeau, B. N. Guo, K. H. Shim, N. Variam, G. Leung, J. Hebb, S. Sharma, C. N. Ni, J. Ren, J. Wen, J. H. Park, H. Chen, S. Chen, M. Hou, D. Tsai, J. Kuo, D. Liao, M. Chudzick, S. H. Lin, H. F. Huang, N. H. Yang, J. F. Lin, C. T. Tsai, G. C. Hung, S. C. Hsu, O. Cheng, J. Y. Wu, T. R. Yew</i>	
8.1 Comprehensive Evaluation of Early Retention (Fast Charge Loss within a Few Seconds) Characteristics in Tube-Type 3-D NAND Flash Memory	61
<i>B. Choi, S. H. Jang, J. Yoon, J. Lee, M. Jeon, Y. Lee, J. Han, J. Lee, D. M. Kim, D. H. Kim, C. Lim, S. Park, S.-J. Choi</i>	
8.2 A Monte Carlo Simulation Method to Predict Large-Density NAND Product Memory Window from Small-Array Test Element Group (TEG) Verified on a 3D NAND Flash Test Chip	63
<i>C.-C. Hsieh, H.-T. Lue, T.-H. Hsu, P.-Y. Du, K.-H. Chiang, C.-Y. Lu</i>	

8.3 Advanced a-VMCO Resistive Switching Memory through Inner Interface Engineering with Wide (>10²) on/off window, Tunable μA-Range Switching Current and Excellent Variability	65
<i>B. Govoreanu, L. Di Piazza, J. Ma, T. Conard, A. Vanleenhove, A. Belmonte, D. Radisic, M. Popovici, A. Velea, A. Redolfi, O. Richard, S. Clima, C. Adelman, H. Bender, M. Jurczak</i>	
8.4 Fully CMOS Compatible 3D Vertical RRAM with Self-Aligned Self-Selective Cell Enabling Sub-5nm Scaling	67
<i>X. Xu, Q. Luo, T. Gong, H. Lv, S. Long, Q. Liu, S. S. Chung, J. Li, M. Liu</i>	
8.5 Te-Based Amorphous Binary OTS Device with Excellent Selector Characteristics for X-Point Memory Applications	69
<i>Y. Koo, K. Baek, H. Hwang</i>	
9.1 Demonstration of a Sub-0.03 μm² High Density 6-T SRAM with Scaled Bulk FinFETs for Mobile SOC Applications Beyond 10nm Node	71
<i>S.-Y. Wu, C. Y. Lin, M. C. Chiang, J. J. Liaw, J. Y. Cheng, C. H. Chang, V. S. Chang, K. H. Pan, C. H. Tsai, C. H. Yao, T. Miyashita, Y. K. Wu, K. C. Ting, C. H. Hsieh, R. F. Tsui, R. Chen, C. L. Yang, H. C. Chang, C. Y. Lee, K. S. Chen, Y. Ku, S. M. Jang</i>	
9.2 First Demonstration of InGaAs/SiGe CMOS Inverters and Dense SRAM Arrays on Si Using Selective Epitaxy and Standard FEOL Processes	73
<i>L. Czornomaz, V. Djara, V. Deshpande, E. O'Connor, M. Sousa, D. Caimi, K. Cheng, J. Fompeyrine</i>	
9.3 Replacement High-K/Metal-Gate High-Ge-Content Strained SiGe FinFETs with High Hole Mobility and Excellent SS and Reliability at Aggressive EOT \sim7Å and Scaled Dimensions Down to Sub-4nm Fin Widths	75
<i>P. Hashemi, T. Ando, K. Balakrishnan, E. Cartier, M. Lofaro, J. A. Ott, J. Bruley, K.-L. Lee, S. Koswatta, S. Dawes, J. Rozen, A. Pyzyna, K. Chan, S. U. Engelmann, D.-G. Park, V. Narayanan, R. T. Mo, E. Leobandung</i>	
9.4 Zero-Thickness Multi Work Function Solutions for N7 Bulk FinFETs	77
<i>L.-å. Ragnarsson, H. Dekkers, P. Matagne, T. Schram, T. Conard, N. Horiguchi, A. V.-Y. Thean</i>	
10.1 Smart Power Technologies Enabling Power SOC and SIP (Invited)	79
<i>S. Pendharkar</i>	
10.2 A Dynamic/Static SRAM Power Management Scheme for DVFS and AVS in Advanced Automotive Infotainment SoCs (Invited)	81
<i>K. Nii, M. Yabuuchi, Y. Ishii, M. Tanaka, M. Igarashi, K. Fukuoka, S. Tanaka</i>	
10.3 A Multiple-String Hybrid LED Driver with 97% Power Efficiency and 0.996 Power Factor	83
<i>L. Li, Y. Gao, P. K. T. Mok</i>	
10.4 A Sine-Reference Band (SRB)-Controlled Average Current Technique for a Phase-Cut Dimmable AC-DC Buck LED Driver without an Electrolytic Capacitor	85
<i>C. Shin, W. Lee, S.-W. Lee, B. Jeong, J. Lee, U. Jang, Y.-G. Kim, S.-H. Lee, J.-S. Bang, G.-H. Cho</i>	
11.1 Overcoming Scaling Barriers through Design Technology CoOptimization (Invited)	87
<i>L. Liebmann, J. Zeng, X. Zhu, L. Yuan, G. Bouche, J. Kye</i>	
11.2 Analog/RF Wonderland: Circuit and Technology Co-Optimization in Advanced FinFET Technology (Invited)	89
<i>F.-L. Hsueh, Y.-C. Peng, C.-H. Chen, T.-J. Yeh, H.-H. Hsieh, C.-H. Chang, S.-L. Liu, M.-C. Chuang, M. Chen</i>	
11.3 200-280GHz CMOS RF Front-End of Transmitter for Rotational Spectroscopy	91
<i>N. Sharma, Q. Zhong, Z. Chen, W. Choi, J. P. McMillan, C. F. Neese, R. Schueler, I. Medvedev, F. De Lucia, K. O</i>	
11.4 Broadband THz Spectroscopic Imaging Based on a Fully-Integrated 4x2 Digital-to-Impulse Radiating Array with a Full-Spectrum of 0.03-1.03THz in Silicon	93
<i>M. M. Assefzadeh, A. Babakhani</i>	
12.1 RTN-Based Defect Tracking Technique: Experimentally Probing the Spatial and Energy Profile of the Critical Filament Region and its Correlation with HfO₂ RRAM Switching Operation and Failure Mechanism	95
<i>Z. Chai, J. Ma, W. Zhang, B. Govoreanu, E. Simoen, J. F. Zhang, Z. Ji, R. Gao, G. Groeseneken, M. Jurczak</i>	
12.2 Robust Cu Atom Switch with over-400°C Thermally Tolerant Polymer-Solid Electrolyte (TT-PSE) for Nonvolatile Programmable Logic	97
<i>K. Okamoto, M. Tada, N. Banno, N. Iguchi, H. Hada, T. Sakamoto, M. Miyamura, Y. Tsuji, R. Nebashi, A. Morioka, X. Bai, T. Sugibayashi</i>	
12.3 Retention, Disturb and Variability Improvements Enabled by Local Chemical-Potential Tuning and Controlled Hour-Glass Filament Shape in a Novel W\WO₃\Al₂O₃\Cu CBRAM	99
<i>L. Goux, A. Belmonte, U. Celano, J. Woo, S. Folkersma, C. Y. Chen, A. Redolfi, A. Fantini, R. Degraeve, S. Clima, W. Vandervorst, M. Jurczak</i>	
12.4 A Novel Low Power Phase Change Memory Using Inter-Granular Switching	101
<i>H. L. Lung, Y. H. Ho, Y. Zhu, W. C. Chien, S. Kim, W. Kim, H. Y. Cheng, A. Ray, M. Brightsky, R. Bruce, C. W. Yeh, C. Lam</i>	

13.1 Smart Solutions for Efficient Dual Strain Integration for Future FDSOI Generations	103
<i>A. Bonneville, C. Le Royer, Y. Morand, S. Reboh, C. Plantier, N. Rambal, J.-P. Pédini, S. Kerdiles, P. Besson, J.-M. Hartmann, D. Marseilhan, B. Mathieu, R. Berthelon, M. Cassé, F. Andrieu, D. Rouchon, O. Weber, F. Boeuf, M. Haond, A. Claverie, M. Vinet</i>	
13.2 High Performance CMOS FDSOI Devices Activated at Low Temperature	105
<i>L. Pasini, P. Batude, J. Lacord, M. Casse, B. Mathieu, B. Sklenard, F. P. Luce, J. Micout, A. Payet, F. Mazen, P. Besson, E. Ghegin, J. Borrel, R. Daubriac, L. Hutin, D. Blachier, D. Barge, S. Chhun, V. Mazzocchi, A. Cros, J.-P. Barnes, Z. Saghi, V. Delaye, N. Rambal, V. Lapras, J. Mazurier, O. Weber, F. Andrieu, L. Brunet, C. Fenouillet-Beranger, Q. Rajhaya, G. Ghibaudo, F. Cristiano, M. Haond, F. Boeuf, M. Vinet</i>	
13.3 High Aspect Ratio InGaAs FinFETs with Sub-20 nm Fin Width	107
<i>A. Vardi, J. Lin, W. Lu, X. Zhao, J. A. Del Alamo</i>	
13.4 Junctionless Gate-All-Around Lateral and Vertical Nanowire FETs with Simplified Processing for Advanced Logic and Analog/RF Applications and Scaled SRAM Cells	109
<i>A. Veloso, B. Parvais, P. Matagne, E. Simoen, T. Huynh-Bao, V. Paraschiv, E. Vecchio, K. Devriendt, E. Rosseel, M. Ercken, B. T. Chan, C. Delvaux, E. Altamirano-Sánchez, J. J. Verstuijs, Z. Tao, S. Suhard, S. Brus, A. Sibaja-Hernandez, N. Waldron, P. Lagrain, O. Richard, H. Bender, A. Chasin, B. Kaczer, T. Ivanov, S. Ramesh, K. De Meyer, J. Ryckaert, N. Collaert, A. Thean</i>	
13.5 Record Mobility ($\mu_{\text{eff}} \sim 3100 \text{ cm}^2/\text{V}\cdot\text{s}$) and Reliability Performance ($V_{\text{ov}} \sim 0.5\text{V}$ for 10yr Operation) of $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOS Devices Using Improved Surface Preparation and a Novel Interfacial Layer	111
<i>A. Vais, A. Alian, L. Nyns, J. Franco, S. Sioncke, V. Putcha, H. Yu, Y. Mols, R. Rooyackers, D. Lin, J. W. Maes, Q. Xie, M. Givens, F. Tang, X. Jiang, A. Mocuta, N. Collaert, K. De Meyer, A. Thean</i>	
14.1 Reliability Study of Perpendicular STT-MRAM As Emerging Embedded Memory Qualified for Reflow Soldering at 260°C	113
<i>M.-C. Shih, C.-Y. Wang, Y.-H. Lee, W. Wang, L. Thomas, H. Liu, J. Zhu, Y.-J. Lee, G. Jan, Y.-J. Wang, T. Zhong, T. Torng, P.-K. Wang, D. Lin, T.-W. Chiang, K.-H. Shen, H. Chuang, W. J. Gallagher</i>	
14.2 Sub-3 ns Pulse with sub-100 μA Switching of 1x-2x nm Perpendicular MTJ for High-Performance Embedded STT-MRAM Towards Sub-20 nm CMOS	115
<i>D. Saida, S. Kashiwada, M. Yakabe, T. Daibou, N. Hase, M. Fukumoto, S. Miwa, Y. Suzuki, H. Noguchi, S. Fujita, J. Ito</i>	
14.3 First Demonstration and Performance Improvement of Ferroelectric HfO_2-Based Resistive Switch with Low Operation Current and Intrinsic Diode Property	117
<i>S. Fujii, Y. Kamimuta, T. Ino, Y. Nakasaki, R. Takaishi, M. Saitoh</i>	
14.4 One-Transistor Ferroelectric Versatile Memory: Strained-Gate Engineering for Realizing Energy-Efficient Switching and Fast Negative-Capacitance Operation	119
<i>Y.-C. Chiu, C.-H. Cheng, C.-Y. Chang, Y.-T. Tang, M.-C. Chen</i>	
14.5 Study of Wake-Up and Fatigue Properties in Doped and Undoped Ferroelectric HfO_2 in Conjunction with Piezo-Response Force Microscopy Analysis	121
<i>S. Shibayama, L. Xu, S. Migita, A. Toriumi</i>	
15.1 Gate-All-Around MOSFETs Based on Vertically Stacked Horizontal Si Nanowires in a Replacement Metal Gate Process on Bulk Si Substrates	123
<i>H. Mertens, R. Ritzenthaler, A. Hikavyy, M. S. Kim, Z. Tao, K. Wostyn, S. A. Chew, A. De Keersgieter, G. Mannaert, E. Rosseel, T. Schram, K. Devriendt, D. Tsvetanova, H. Dekkers, S. Demuyne, A. Chasin, E. Van Besien, A. Dangol, S. Godny, B. Douhard, N. Bosman, O. Richard, J. Geypen, H. Bender, K. Barla, D. Mocuta, N. Horiguchi, A. V.-Y. Thean</i>	
15.2 InAs Nanowire GAA n-MOSFETs with 12-15 nm Diameter	125
<i>T. Vasen, P. Ramvall, A. Afzal, C. Thelander, K. A. Dick, M. Holland, G. Doornbos, S. W. Wang, R. Oxland, G. Vellianitis, M. J. H. Van Dal, B. Duriez, J.-R. Ramirez, R. Droopad, L.-E. Wernersson, L. Samuelson, T.-K. Chen, Y.-C. Yeo, M. Passlack</i>	
15.3 InGaAs Nanowire MOSFETs with $\text{ION} = 555 \mu\text{A}/\mu\text{m}$ at $\text{IOFF} = 100 \text{ nA}/\mu\text{m}$ and $V_{\text{DD}} = 0.5 \text{ V}$	127
<i>C. B. Zota, F. Lindelöw, L.-E. Wernersson, E. Lind</i>	
15.4 Top-Down InGaAs Nanowire and Fin Vertical FETs with Record Performance	129
<i>S. Ramesh, T. Ivanov, E. Camerotto, N. Sun, J. Franco, A. Sibaja-Hernandez, R. Rooyackers, A. Alian, J. Loo, A. Veloso, A. Milenin, D. Lin, P. Favia, H. Bender, N. Collaert, A. V.-Y. Thean, K. De Meyer</i>	
15.5 Scalability of InGaAs Gate-All-Around FET Integrated on 300mm Si platform: Demonstration of Channel Width Down to 7nm and L_g Down to 36nm	131
<i>X. Zhou, N. Waldron, G. Boccardi, F. Sebaai, C. Merckling, G. Eneman, S. Sioncke, L. Nyns, A. Opdebeeck, J. W. Maes, Q. Xie, M. Givens, F. Tang, X. Jiang, W. Guo, B. Kunert, L. Teugels, K. Devriendt, A. S. Hernandez, J. Franco, D. Van Dorp, K. Barla, N. Collaert, A. V.-Y. Thean</i>	
16.1 RTN and Low Frequency Noise on Ultra-Scaled Near-Ballistic Ge Nanowire nMOSFETs	133
<i>W. Wu, H. Wu, M. Si, N. Conrad, Y. Zhao, P. D. Ye</i>	
16.2 Statistical Limits of Contact Resistivity Due to Atomistic Variation in Nanoscale Contacts	135
<i>G. Shine, C. E. Weber, K. C. Saraswat</i>	

16.3 Variability-Aware TCAD Based Design-Technology Co-Optimization Platform for 7nm Node Nanowire and Beyond	137
<i>Y. Wang, B. Cheng, X. Wang, E. Towie, C. Riddet, A. R. Brown, S. M. Amoroso, L. Wang, D. Reid, X. Liu, J. Kang, A. Asenov</i>	
16.4 Random Telegraph Noise (RTN) in 14nm Logic Technology: High Volume Data Extraction and Analysis	139
<i>S. Dongaonkar, M. D. Giles, A. Kornfeld, B. Grossnickle, J. Yoon</i>	
16.5 Design / Technology Co-Optimization of Strain-Induced Layout Effects in 14nm UTBB-FDSOI CMOS: Enablement and Assessment of Continuous-RX Designs	141
<i>R. Berthelon, F. Andrieu, E. Josse, R. Bingert, O. Weber, E. Serret, A. Aurand, S. Delmedico, V. Farys, C. Bernicot, E. Bechet, E. Bernard, T. Poiroux, D. Rideau, P. Scheer, E. Baylac, P. Perreau, M. A. Jaud, J. Lacord, E. Petitprez, A. Pofelski, S. Ortolland, P. Sardin, D. Dutartre, A. Claverie, M. Vinet, J. C. Marin, M. Haond</i>	
17.1 On-Chip Interconnect Trends, Challenges and Solutions: How to Keep RC and Reliability Under Control (Invited)	143
<i>Z. Tokci, I. Ciofi, P. Roussel, P. Debacker, P. Raghavan, M. H. Van Der Veen, N. Jourdan, C. J. Wilson, V. V. Gonzalez, C. Adelman, L. Wen, K. Croes, O. V. P. K. Moors, M. Krishtab, S. Armini, J. Bömmels</i>	
17.2 Production-Worthy WOW 3D Integration Technology Using Bumpless Interconnects and Ultra-Thinning Processes (Invited)	145
<i>T. Ohba</i>	
17.3 First Demonstration of a CMOS over CMOS 3D VLSI CoolCube™ Integration on 300mm Wafers	147
<i>L. Brunet, P. Batude, C. Fenouillet-Beranger, P. Besombes, L. Hortemel, F. Ponthenier, B. Previtali, C. Tabone, A. Royer, C. Agraffail, C. Euvrard-Colnat, A. Seignard, C. Morales, F. Fournel, L. Benaissa, T. Signamarcheix, P. Besson, M. Jourdan, R. Kachtouli, V. Benevent, J.-M. Hartmann, C. Comboroure, N. Allouti, N. Posseme, C. Vizioz, C. Arvet, S. Barnola, S. Kerdiles, L. Baud, L. Pasini, C.-M. V. Lu, F. Deprat, A. Toffoli, G. Romano, C. Guedj, V. Delaye, F. Boeuf, O. Faynot, M. Vinet</i>	
17.4 A Highly Scalable Poly-Si Junctionless FETs Featuring a Novel Multi-Stacking Hybrid P/N Layer and Vertical Gate with Very High Ion/Ioff for 3D Stacked ICs	149
<i>Y.-C. Cheng, H.-B. Chen, C.-Y. Chang, C.-H. Cheng, Y.-J. Shih, Y.-C. Wu</i>	
18.1 Direct Three-Dimensional Observation of the Conduction in Poly-Si and In_{1-x}Ga_xAs 3D NAND Vertical Channels	151
<i>U. Celano, E. Capogreco, J. G. Lisoni, A. Arreghini, B. Kunert, W. Guo, G. Van Den Bosch, J. Van Houdt, K. De Meyer, A. Furnemont, W. Vandervorst</i>	
18.2 Four-Layer 3D Vertical RRAM Integrated with FinFET as a Versatile Computing Unit for Brain-Inspired Cognitive Information Processing	153
<i>H. Li, K.-S. Li, C.-H. Lin, J.-L. Hsu, W.-C. Chiu, M.-C. Chen, T.-T. Wu, J. Sohn, S. B. Eryilmaz, J.-M. Shieh, W.-K. Yeh, H.-S. P. Wong</i>	
18.3 Novel RRAM-Enabled 1T1R Synapse Capable of Low-Power STDP via Burst-Mode Communication and Real-Time Unsupervised Machine Learning	155
<i>S. Ambrogio, S. Balatti, V. Milo, R. Carboni, Z. Wang, A. Calderoni, N. Ramaswamy, D. Ielmini</i>	
18.4 A ReRAM-Based Physically Unclonable Function with Bit Error Rate < 0.5% after 10 Years at 125°C for 40nm Embedded Application	157
<i>Y. Yoshimoto, Y. Katoh, S. Ogasahara, Z. Wei, K. Kouno</i>	
19.1 Gate Stack Solutions in Gate-First FDSOI Technology to meet High Performance, Low Leakage, VT Centering and Reliability Criteria	159
<i>O. Weber, E. Josse, X. Garros, M. Rafik, X. Federspiel, C. Diouf, A. Toffoli, S. Zoll, O. Gourhant, V. Joseph, C. Suarez-Segovia, F. Domengie, V. Beugin, B. Saidi, M. Gros-Jean, P. Perreau, J. Mazurier, E. Richard, M. Haond</i>	
19.2 A New Variation Plot to Examine the Interfacial-Dipole Induced Work-Function Variation in Advanced High-k Metal-Gate CMOS Devices	161
<i>E. R. Hsieh, Y. D. Wang, S. S. Chung, J. C. Ke, C. W. Yang, S. Hsu</i>	
19.3 Novel N/PFET Vt Control by TiN Plasma Nitridation for Aggressive Gate Scaling	163
<i>M. Togo, W. H. Tong, X. Zhang, D. H. Triyoso, J. Lian, Y. M. Randriamihja, S. Uppal, S. Dag, E. C. Silva, M. Kota, T. Shimizu, S. Patil, M. Eller, S. Samavedam</i>	
19.4 Complete Extraction of Defect Bands Responsible for Instabilities in n and pFinFETs	165
<i>G. Rzepa, M. Walil, W. Goes, B. Kaczer, J. Franco, T. Chiarella, N. Horiguchi, T. Grasser</i>	
20.1 Low-Power, High-Performance S-NDR Oscillators for Stereo (3D) Vision Using Directly-Coupled Oscillator Networks	167
<i>A. A. Sharma, Y. Kesim, M. Shulaker, C. Kuo, C. Augustine, H. S.-P. Wong, S. Mitra, M. Skowronski, J. A. Bain, J. A. Weldon</i>	
20.2 Ultra Low Power Coupled Oscillator Arrays for Computer Vision Applications	169
<i>N. Shukla, W.-Y. Tsai, M. Jerry, M. Barth, V. Narayanan, S. Datta</i>	
20.3 A 512x576 65-nm CMOS ISFET Sensor for Food Safety Screening with 123.8 mV/pH Sensitivity and 0.01 pH Resolution	171
<i>Y. Jiang, X. Liu, T. C. Dang, M. Yan, H. Yu, J.-C. Huang, C.-H. Hsieh, T.-T. Chen</i>	

20.4 Integration of Neural Sensing Microsystem with TSV-Embedded Dissolvable μ-Needles Array, Biocompatible Flexible Interposer, and Neural Recording Circuits	173
<i>Y.-C. Huang, Y.-C. Hu, P.-T. Huang, S.-L. Wu, Y.-H. You, J.-M. Chen, Y.-Y. Huang, H.-C. Chang, Y.-H. Lin, J.-R. Duann, T.-W. Chiu, W. Hwang, C.-T. Chuang, J.-C. Chiou, K.-N. Chen</i>	
21.1 Enabling High-Performance Heterogeneous TFET/CMOS Logic with Novel Circuits Using TFET Unidirectionality and Low-VDD Operation	175
<i>D. H. Morris, K. Vaidyanathan, U. E. Avci, H. Liu, T. Karnik, I. A. Young</i>	
21.2 Performance Improvement of $\text{In}_x\text{Ga}_{1-x}\text{As}$ Tunnel FETs with Quantum Well and EOT Scaling	177
<i>D. H. Ahn, S. M. Ji, M. Takenaka, S. Takagi</i>	
21.3 Complementary III-V Heterojunction Lateral NW Tunnel FET Technology on Si	179
<i>D. Cutaia, K. E. Moselund, H. Schmid, M. Borg, A. Olziersky, H. Riel</i>	
21.4 Phase-Transition-FET Exhibiting Steep Switching Slope of 8mV/Decade and 36% Enhanced ON Current	181
<i>J. Frougier, N. Shukla, D. Deng, M. Jerry, A. Aziz, L. Liu, G. Lavallee, T. S. Mayer, S. Gupta, S. Datta</i>	
21.5 Circuit Performance Analysis of Negative Capacitance FinFETs	183
<i>S. Khandelwal, A. I. Khan, J. P. Duarte, A. B. Sachid, S. Salahuddin, C. Hu</i>	
22.1 White Spots Reduction by Ultimate Proximity Metal Gettering at Carbon Complexes Formed underneath Contact Area in CMOS Image Sensors	185
<i>T. Yamaguchi, T. Yamashita, T. Kamino, Y. Goto, T. Kuroi, M. Matsuura</i>	
22.2 Enabling Monolithic 3D Image Sensor Using Large-Area Monolayer Transition Metal Dichalcogenide and Logic/Memory Hybrid 3D⁺IC	187
<i>C.-C. Yang, K.-C. Chiu, C.-T. Chou, C.-N. Liao, M.-H. Chuang, T.-Y. Hsieh, W.-H. Huang, C.-H. Shen, J.-M. Shieh, W.-K. Yeh, Y.-H. Chen, M.-C. Wu, Y.-H. Lee</i>	
22.3 Germanium-Tin Heterojunction Phototransistor: Towards High-Efficiency Low-Power Photodetection in Short-Wave Infrared Range	189
<i>W. Wang, Y. Dong, S. Y. Lee, W. K. Loke, X. Gong, S.-F. Yoon, G. Liang, Y.-C. Yeo</i>	
22.4 Novel Pixel Structure with Stacked Deep Photodiode to Achieve High NIR Sensitivity and High MTF	191
<i>H. Takahashi, H. Tanaka, M. Oda, M. Ando, N. Niisoe, S. Kawai, T. Asano, M. Sudo, M. Yoshita, T. Yamada</i>	
22.5 Back-Illuminated Voltage-Domain Global Shutter CMOS Image Sensor with 3.75μm Pixels and Dual in-Pixel Storage Nodes	193
<i>L. Stark, J. M. Raynor, F. Lalanne, R. K. Henderson</i>	
Author Index	